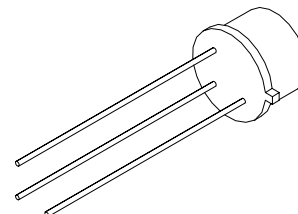




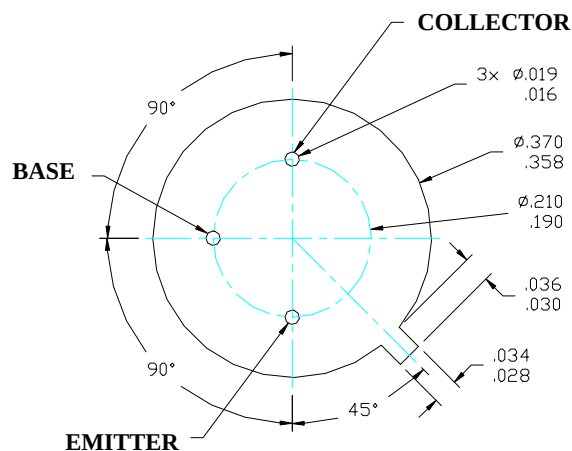
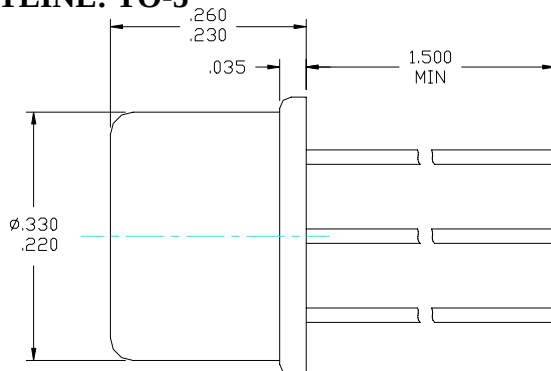
PRELIMINARY

SOLID STATE DEVICES, INC.14005 Stage Road * Santa Fe Springs, Ca 90670
Phone: (562) 404-4474 * Fax: (562) 404-1773**DESIGNER'S DATA SHEET****FEATURES:**

- BV_{CEO} 400V.
- Fast Switching.
- High Frequency.
- Low Saturation Voltage.
- 200°C Operating, Gold Eutectic Die Attach.
- Designed for Complementary Use with SFT6800.

SFT1192**2 AMP
500 VOLTS
PNP TRANSISTOR****TO-5**

MAXIMUM RATINGS	SYMBOL	VALUE	UNITS
Collector-Emitter Voltage	V_{CEO}	400	Volts
Collector-Base Voltage	V_{CBO}	500	Volts
Emitter-Base Voltage	V_{EBO}	10	Volts
Collector Current	I_C	2	Amps
Base Current	I_B	0.5	Amps
Total Device Dissipation @ $T_C=100^\circ\text{C}$ Derate above 100°C	P_D	6 150	W mW/°C
Operating and Storage Temperature	T_J, T_{STG}	-65 to +200	°C
Thermal Resistance, Junction to Case	$R_{\theta JC}$	15	°C/W

CASE OUTLINE: TO-5

NOTE: All specifications are subject to change without notification.
SCD's for these devices should be reviewed by SSDI prior to release.

DATA SHEET #: TR0004B

SFT1192

PRELIMINARY

**SOLID STATE DEVICES, INC.**

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ELECTRICAL CHARACTERISTICS		SYMBOL	MIN	MAX	UNITS
Collector-Emitter Breakdown Voltage ($I_C = 5mA_{DC}$)		BV_{CEO}	400	-	V
Collector-Base Breakdown Voltage ($I_C = 100\mu A_{DC}$)		BV_{CBO}	500	-	V
Emitter-Base Breakdown Voltage ($I_E = 20\mu A_{DC}$)		BV_{EBO}	10	-	V
Collector Cutoff Current ($V_{CB} = 450V_{DC}$)		I_{CBO}	-	1.0	μA
Collector Cutoff Current ($V_{CE} = 400V_{DC}$, $V_{EB} = 1.5V_{DC}$)		I_{CEV}	-	10	μA
Emitter Cutoff Current ($V_{EB} = 6V_{DC}$)		I_{EBO}	-	10	μA
DC Current Gain* ($V_{CE} = 10V_{DC}$)	($I_C = 1.0mA_{DC}$)	H_{FE}	80	-	
	($I_C = 50mA_{DC}$)		60	-	
	($I_C = 500mA_{DC}$)		40	-	
Collector-Emitter Saturation Voltage* ($I_C = 50mA_{DC}$, $I_B = 5mA_{DC}$) ($I_C = 500mA_{DC}$, $I_B = 50mA_{DC}$)		$V_{CE(SAT)}$	- -	0.4 1.0	V_{DC}
Base-Emitter Saturation Voltage* ($I_C = 50mA_{DC}$, $I_B = 5mA_{DC}$) ($I_C = 500mA_{DC}$, $I_B = 50mA_{DC}$)		$V_{BE(SAT)}$	- -	1.5 2.0	V_{DC}
Current Gain Bandwidth Product ($I_C = 70mA_{DC}$, $V_{CE} = 30V_{DC}$, $f = 20MHz$)		f_T	50	-	MHz
Output Capacitance ($V_{CB} = 20V_{DC}$, $I_E = 0A_{DC}$, $f = 1.0MHz$)		C_{ob}	-	75	pf
Input Capacitance ($V_{BE} = 2V_{DC}$, $I_C = 0A_{DC}$, $f = 1.0MHz$)		C_{ib}	-	300	pf
Turn On Time	(V _{CC} = 100V _{DC} , I _C = 500mA _{DC} , V _{EB(OFF)} = 3.7V _{DC} , I _{B1} = I _{B2} = 50mA _{DC})	$t_{(on)}$	-	250	ns
Turn Off Time		$t_{(off)}$	-	2500	ns

*Pulse Test: Pulse Width = 300 μs , Duty Cycle = 2%